

RESEARCH AREA 3 - Quantum Science and technologies - 2022

"Orbital selective switching of ferromagnetism in an oxide quasi two-dimensional electron gas"

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Multi-orbital physics in quasi-two-dimensional electron gases (q2DEGs) triggers intriguing phenomena not observed in bulk materials, such as unconventional superconductivity and magnetism. Here, we investigate the mechanism of orbital selective switching of the spin-polarization in the oxide q2DEG formed at the (001) interface between the LaAlO₃, EuTiO₃ and SrTiO₃ band insulators. By using density functional theory calculations, transport, magnetic and x-ray spectroscopy measurements, we find that the filling of titanium-bands with $3d_{xz}/3d_{yz}$ orbital character in the EuTiO₃ layer and at the interface with SrTiO₃ induces an antiferromagnetic to ferromagnetic switching of the exchange interaction between Eu-4f⁷ magnetic moments. The results explain the observation of the carrier density-dependent ferromagnetic correlations and anomalous Hall effect in this q2DEG, and demonstrate how combined theoretical and experimental approaches can lead to a deeper understanding of emerging electronic phases and serve as a guide for the materials design of advanced electronic applications.

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Fig. 1: (a) Sketch of the LAO/ETO/STO heterostructure. (b) Sheet resistance vs. temperature as a function of the gate voltage Vg. The arrow indicates increasing values of Vg from -30 to 30 V and 2D carrier density. (C) Eu- XMCD (scatter data) and SQUID magnetization (continuous lines) as function of the magnetic field parallel (red) and perpendicular (black) to the interface. The data are normalized to the saturation value.





